/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

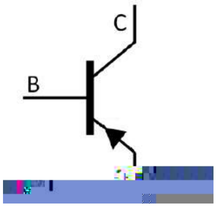
MJD41C

Complement to MJD41C.

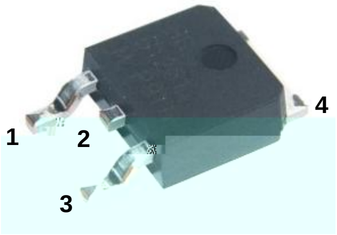
/ Applications

Medium power linear switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-6.0	A
Base Current - Continuous	I_B	-2.0	A
Collector Power Dissipation	P_D	1.75	W
Collector Power Dissipation	P_D(T_C=25)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-30mA I_B=0	-100			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=-60V I_B=0			-50	A
Collector Cut-Off Current	I_{CES}	V_{CE}=-100V V_{BE}=0			-10	A
Emitter Cut-Off Current	I					

/ Electrical Characteristic Curve

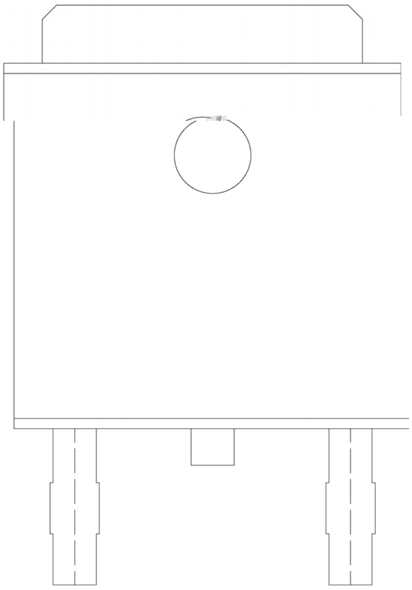
/ Package Dimensions

4.75	
2.95	
1.25	1.75
0.60	0.90
0.00	0.10

b1	0.45	0.55	L1	9.45
C	0.45	0.55	L2	
D	6.45	6.75	L3	
D1	5.10	5.50	K	

TO-252

/ Marking Instructions



BR

MJD42C

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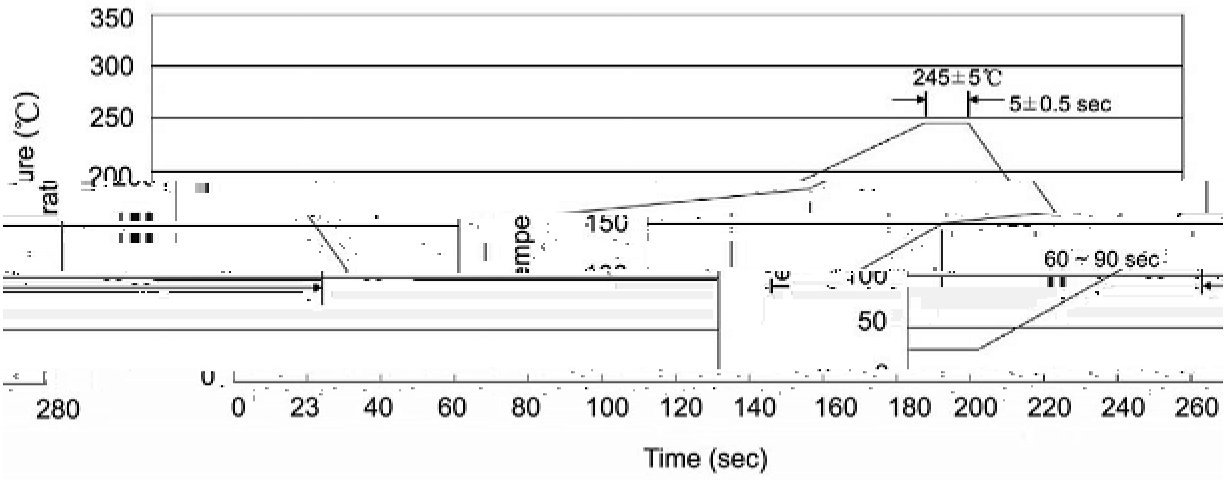
Note:

BR:

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec;
2 245±5 5±0.5sec;
3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:245±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec.

Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension (unit mm^3)